TOSHIBA TRANSISTOR SILOCON NPN EPITAXIAL PLANAR TYPE

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TV VHF RF AMPLIFIER APPLICATIONS

• High Gain : $G_{pe} = 24dB$ (Typ.) (f = 200MHz)

• Low Noise : NF = 2.0dB (Typ.) (f = 200MHz)

• Excellent Forward AGC Characteristics

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	30	V
Collector-Emitter Voltage	v_{CEO}	30	V
Emitter-Base Voltage	$V_{ m EBO}$	3	V
Collector Current	$I_{\mathbf{C}}$	20	mA
Base Current	$I_{\mathbf{B}}$	10	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	100	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Weight: 0.006g

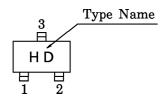
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 25V, I_{E} = 0$	_	_	100	nA
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=2V, I_{C}=0$	_		100	nA
Collector Emitter Breakdown Voltage	V _(BR) CEO	$I_{C}=1$ mA, $I_{B}=0$	30	1	_	V
DC Current Gain	${ m h_{FE}}$	$V_{CE}=10V, I_{C}=2mA$	60	150	300	_
Reverse Transfer Capacitance	$\mathrm{c_{re}}$	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	0.35	0.5	pF
Transition Frequency	${ m f_T}$	$V_{CE}=10V, I_{C}=2mA$	400	650	_	MHz
Power Gain	$G_{ m pe}$	$V_{CC}=12V, V_{AGC}=1.4V$	20	24	28	dB
Noise Figure	NF	f=200MHz (Fig.1)	_	2.0	3.2	dB
AGC Voltage (Note)	$v_{ m AGC}$	V _{CC} =12V, GR=30dB f=200MHz	3.6	4.4	5.1	V

(Note) $V_{\mbox{AGC}}$ measured by test circuit shown in Fig.1 when power gain is reduced to 30dB compared that of $V_{\mbox{AGC}}$ at 1.4V.

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MARKING



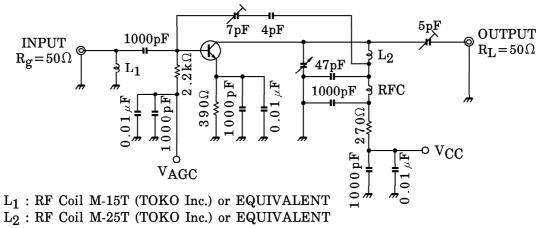
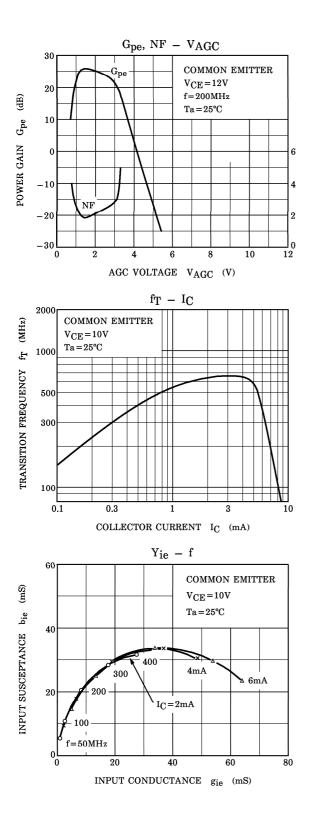


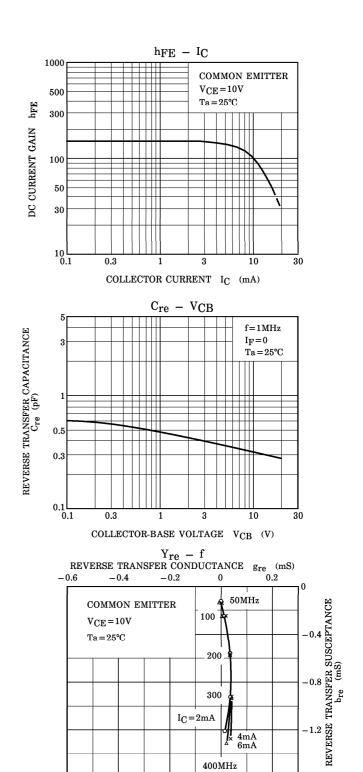
Fig.1 200MHz G_{pe} , NF TEST CIRCUIT



(dB)

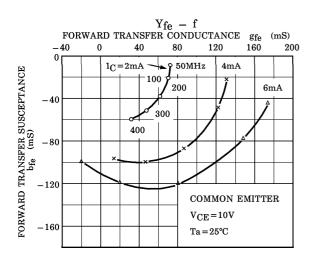
NF

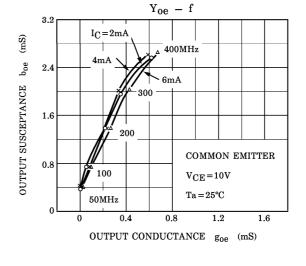
NOISE FIGURE

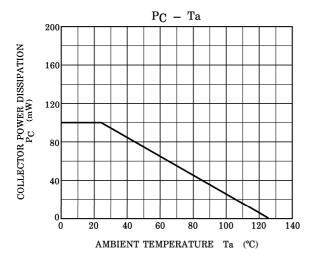


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400MHz







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